

2N7002L, 2V7002L

Small Signal MOSFET

60 V, 115 mA, N-Channel SOT-23



ON Semiconductor®

<http://onsemi.com>

Features

- 2V Prefix for Automotive and Other Applications Requiring Site and Change Controls
- AEC Qualified – 2V7002L
- PPAP Capable – 2V7002L
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V_{DGR}	60	Vdc
Drain Current – Continuous $T_C = 25^\circ\text{C}$ (Note 1) $T_C = 100^\circ\text{C}$ (Note 1) – Pulsed (Note 2)	I_D I_{DM}	± 115 ± 75 ± 800	mAdc
Gate-Source Voltage – Continuous – Non-repetitive ($t_p \leq 50 \mu\text{s}$)	V_{GS} V_{GSM}	± 20 ± 40	Vdc Vpk

THERMAL CHARACTERISTICS

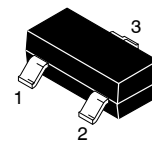
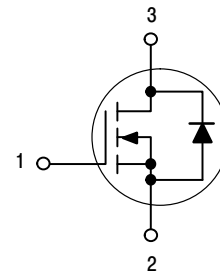
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 3) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Note 4) Alumina Substrate, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to the Recommended Operating Conditions may affect device reliability.

1. The Power Dissipation of the package may result in a lower continuous drain current.
2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
3. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
4. Alumina = $0.4 \times 0.3 \times 0.025$ in 99.5% alumina.

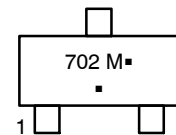
$V_{(BR)DSS}$	$R_{DS(on) \text{ MAX}}$	$I_D \text{ MAX}$
60 V	$7.5 \Omega @ 10 \text{ V}, 500 \text{ mA}$	115 mA

N-Channel



SOT-23
CASE 318
STYLE 21

MARKING DIAGRAM



702 = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
2N7002LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
2N7002LT3G		10,000 Tape & Reel
2V7002LT1G	SOT-23 (Pb-Free)	3000 Tape & Reel
2V7002LT3G		10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2N7002L, 2V7002L

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ($V_{GS} = 0, I_D = 10 \mu\text{Adc}$)	$V_{(BR)DSS}$	60	-	-	Vdc
Zero Gate Voltage Drain Current ($V_{GS} = 0, V_{DS} = 60 \text{ Vdc}$)	I_{DSS}	$T_J = 25^\circ\text{C}$	-	-	1.0
		$T_J = 125^\circ\text{C}$	-	-	500
Gate-Body Leakage Current, Forward ($V_{GS} = 20 \text{ Vdc}$)	I_{GSSF}	-	-	100	nAdc
Gate-Body Leakage Current, Reverse ($V_{GS} = -20 \text{ Vdc}$)	I_{GSSR}	-	-	-100	nAdc

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 250 \mu\text{Adc}$)	$V_{GS(th)}$	1.0	-	2.5	Vdc
On-State Drain Current ($V_{DS} \geq 2.0 V_{DS(on)}, V_{GS} = 10 \text{ Vdc}$)	$I_{D(on)}$	500	-	-	mA
Static Drain-Source On-State Voltage ($V_{GS} = 10 \text{ Vdc}, I_D = 500 \text{ mAdc}$) ($V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mAdc}$)	$V_{DS(on)}$	-	-	3.75	Vdc
		-	-	0.375	
Static Drain-Source On-State Resistance ($V_{GS} = 10 \text{ V}, I_D = 500 \text{ mAdc}$) ($V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mAdc}$)	$r_{DS(on)}$	$T_C = 25^\circ\text{C}$	-	-	7.5
		$T_C = 125^\circ\text{C}$	-	-	13.5
		$T_C = 25^\circ\text{C}$	-	-	7.5
		$T_C = 125^\circ\text{C}$	-	-	13.5
Forward Transconductance ($V_{DS} \geq 2.0 V_{DS(on)}, I_D = 200 \text{ mAdc}$)	g_{FS}	80	-	-	mS

DYNAMIC CHARACTERISTICS

Input Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{iss}	-	-	50	pF
Output Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{oss}	-	-	25	pF
Reverse Transfer Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{rss}	-	-	5.0	pF

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$(V_{DD} = 25 \text{ Vdc}, I_D \cong 500 \text{ mAdc}, R_G = 25 \Omega, R_L = 50 \Omega, V_{gen} = 10 \text{ V})$	$t_{d(on)}$	-	-	20	ns
Turn-Off Delay Time		$t_{d(off)}$	-	-	40	ns

BODY-DRAIN DIODE RATINGS

Diode Forward On-Voltage ($I_S = 11.5 \text{ mAdc}, V_{GS} = 0 \text{ V}$)	V_{SD}	-	-	-1.5	Vdc
Source Current Continuous (Body Diode)	I_S	-	-	-115	mAdc
Source Current Pulsed	I_{SM}	-	-	-800	mAdc

5. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

TYPICAL ELECTRICAL CHARACTERISTICS

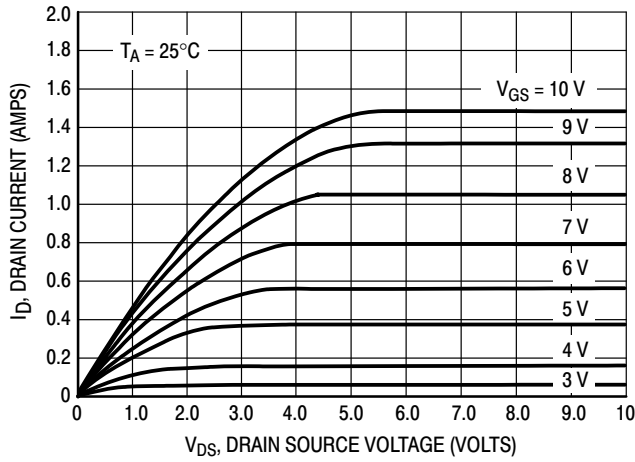


Figure 1. Ohmic Region

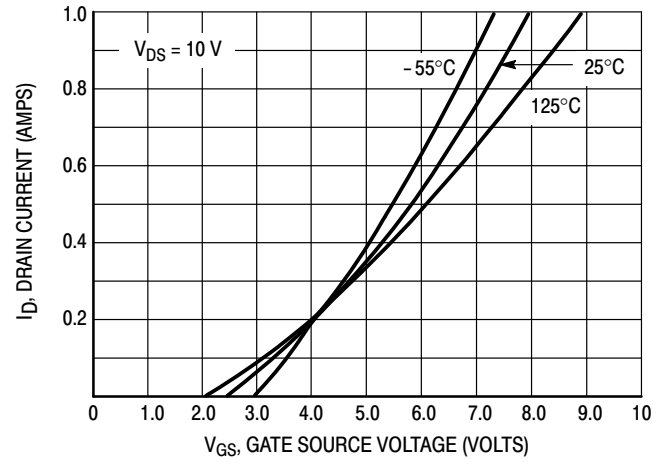


Figure 2. Transfer Characteristics

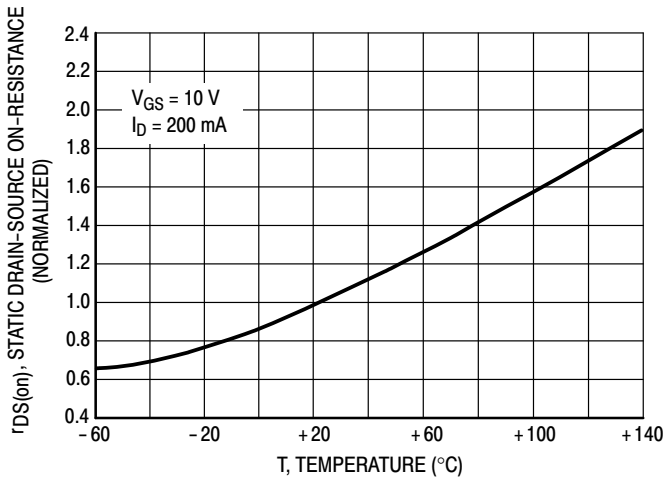


Figure 3. Temperature versus Static Drain-Source On-Resistance

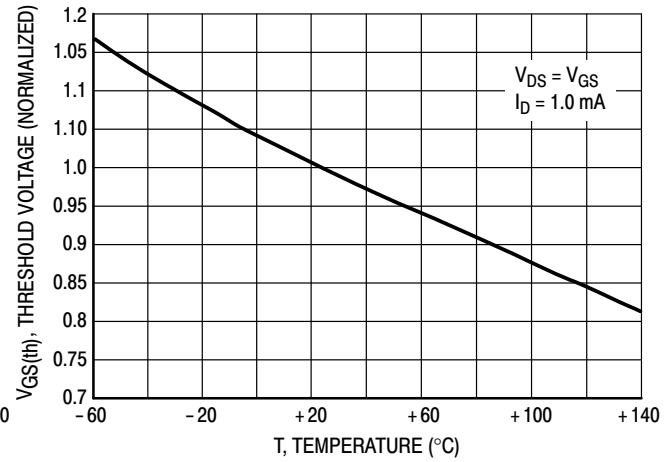
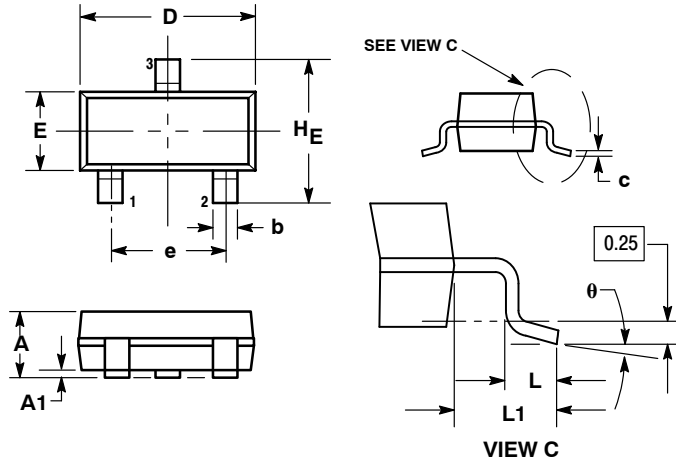


Figure 4. Temperature versus Gate Threshold Voltage

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PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP



NOTES:

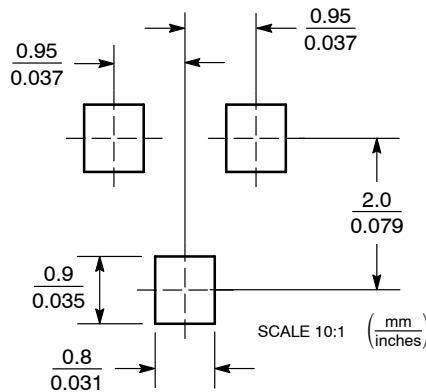
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 21:

- PIN 1. GATE
- SOURCE
- DRAIN

SOLDERING FOOTPRINT



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